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Mark H. Somervell

Thomas I. Wallow

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The CID number appears on each page of the manuscript. The complete citation is used on the first page, and an abbreviated version on subsequent pages. Numbers in the index correspond to the last two digits of the six-digit CID number.

Contents

xiii Conference Committee

KEYNOTE SESSION

- 8325 03 **Factors that determine the optimum dose for sub-20nm resist systems: DUV, EUV, and e-beam options (Keynote Paper)** [8325-02]
M. Preil, GLOBALFOUNDRIES Inc. (United States)

NEGATIVE TONE PROCESSING

- 8325 04 **Optical performance comparison between negative tone development and positive tone development** [8325-03]
S.-H. Yang, E. S. Kim, S. Moon, S. Lee, S.-W. Choi, J. Choi, SAMSUNG Electronics Co., Ltd. (Korea, Republic of)
- 8325 05 **Functional resist materials for negative tone development in advanced lithography** [8325-04]
S. Tarutani, K. Fujii, K. Yamamoto, K. Iwato, M. Shirakawa, FUJIFILM Corp. (Japan)
- 8325 06 **Assessment of negative tone development challenges** [8325-05]
S. S. Mehta, GLOBALFOUNDRIES Inc. (United States); Y. Xu, IBM Corp. (United States); G. Landie, STMicroelectronics (United States); V. Chauhan, GLOBALFOUNDRIES Inc. (United States); S. D. Burns, P. Lawson, IBM Corp. (United States); B. Hamieh, STMicroelectronics (United States); J. Wandell, GLOBALFOUNDRIES Inc. (United States); M. Glodde, IBM Corp. (United States); Y. Y. Sun, M. Kelling, GLOBALFOUNDRIES Inc. (United States); A. Thomas, IBM Corp. (United States); J. S. Kim, GLOBALFOUNDRIES Inc. (United States); J. Chen, IBM Corp. (United States); H. Kato, Toshiba America Electronic Components, Inc. (United States); C. Tseng, C.-S. Koay, IBM Corp. (United States); Y. Matsui, Renesas (United States); M. Burkhardt, Y. Yin, D. Horak, S.-T. Chen, IBM Corp. (United States); Y. Mignot, Y. Loquet, STMicroelectronics (United States); M. Colburn, J. Arnold, T. Spooner, IBM Corp. (United States); L. Huli, D. Hetzer, Tokyo Electron Technology Ctr., America, LLC (United States); J. Cantone, GLOBALFOUNDRIES Inc (United States); S. Kawakami, S. Dunn, Tokyo Electron Technology Ctr., America, LLC (United States)
- 8325 07 **Evolution of negative tone development photoresists for ArF lithography** [8325-07]
M. Reilly, C. Andes, T. Cardolaccia, Y. S. Kim, J. K. Park, The Dow Chemical Co. (United States)

EUV: JOINT SESSION WITH CONFERENCE 8322

- 8325 08 **Optimization of low-diffusion EUV resist for linewidth roughness and pattern collapse on various substrates** [8325-08]
J. W. Thackeray, J. F. Cameron, M. Wagner, S. Coley, O. Ongayi, The Dow Chemical Co. (United States); W. Montgomery, D. Lovell, College of Nanoscale Science & Engineering, Univ. at Albany (United States); J. Biafore, KLA-Tencor Corp. (United States); V. Chakrapani, A. Ko, Tokyo Electron Technology Ctr., America, LLC (United States)
- 8325 09 **EUV resist materials for 20nm and below half-pitch applications** [8325-09]
H. Tsubaki, S. Tarutani, H. Takizawa, T. Goto, FUJIFILM Corp. (Japan)
- 8325 0A **EUV resist development for 16nm half pitch** [8325-10]
K. Maruyama, H. Nakagawa, S. Sharma, Y. Hishiro, JSR Micro, Inc. (United States); M. Shimizu, T. Kimura, JSR Corp. (Japan)

OPTICAL EXTENSIONS

- 8325 0B **Overview: continuous evolution on double-patterning process** [8325-11]
H. Yaegashi, K. Oyama, A. Hara, S. Natori, S. Yamauchi, Tokyo Electron Ltd. (Japan)
- 8325 0C **CD uniformity improvement on the self-aligned spacer double-patterning process by resist material modification** [8325-12]
K. Ohmori, N. Motoike, Tokyo Ohka Kogyo Co., Ltd. (Japan); H. Yaegashi, K. Oyama, Tokyo Electron Ltd. (Japan)
- 8325 0D **SADP for BEOL using chemical slimming with resist mandrel for beyond 22nm nodes** [8325-13]
L. Jang, S. Raghunathan, E. T. Ryan, J. Kye, H. J. Levinson, GLOBALFOUNDRIES Inc. (United States); S. Dunn, Tokyo Electron America, Inc. (United States); D. Hetzer, S. Kawakami, L. Huli, Tokyo Electron Technology Ctr., America, LLC (United States)
- 8325 0G **Comparison of directed self-assembly integrations** [8325-16]
M. Somervell, Tokyo Electron America, Inc. (United States); R. Gronheid, IMEC (Belgium); J. Hooge, K. Nafus, Tokyo Electron America, Inc. (United States); P. Rincon Delgadillo, C. Thode, Univ. of Wisconsin-Madison (United States); T. Younkin, Intel Corp. (Belgium); K. Matsunaga, Tokyo Electron Kyushu Ltd. (Japan); B. Rathsack, S. Scheer, Tokyo Electron America, Inc. (United States); P. Nealey, Univ. of Wisconsin-Madison (United States)

SIMULATION OF RESIST PROCESSES

- 8325 0H **Application of stochastic modeling to resist optimization problems** [8325-17]
J. J. Biafore, M. D. Smith, KLA-Tencor Corp. (United States)
- 8325 0I **Correlated surface roughening during photoresist development** [8325-18]
C. A. Mack, Lithoguru.com (United States)

- 8325 0J **Mesoscale simulation of the line-edge structure during positive and negative tone resist development process** [8325-19]
H. Morita, National Institute of Advanced Industrial Science and Technology (Japan);
I. Okabe, Intel Kabushiki Kaisha (Japan); S. Agarwal, V. K. Singh, Intel Corp. (United States)
- 8325 0K **Line-pattern collapse mitigation status for EUV at 32nm HP and below** [8325-20]
M. Carcasi, D. Bassett, W. Printz, Tokyo Electron America, Inc. (United States); S. Kawakami,
Tokyo Electron Technology Ctr., America, LLC (United States); Y. Miyata, Tokyo Electron
Kyushu Ltd. (Japan)
- 8325 0L **Simultaneous calibration of acid diffusion and developer loading parameters for computational lithography** [8325-21]
A. Parikh, Texas Instruments Inc. (United States)

RESIST FUNDAMENTALS

- 8325 0M **Investigation of acid diffusion during laser spike annealing with systematically designed photoacid generators** [8325-22]
M. Krysak, B. Jung, M. O. Thompson, C. K. Ober, Cornell Univ. (United States)
- 8325 0N **Deprotection reaction kinetics in chemically amplified photoresists determined by sub-millisecond post exposure bake** [8325-23]
B. Jung, C. K. Ober, M. O. Thompson, Cornell Univ. (United States)
- 8325 0O **Contrast improvement with balanced diffusion control of PAG and PDB** [8325-24]
S. F. Chen, L. L. Chang, Y. H. Chang, C. C. Huang, C. Y. Chang, Y. Ku, Taiwan Semiconductor
Manufacturing Co. Ltd. (Taiwan)
- 8325 0P **An in situ analysis of the resist pattern formation process** [8325-25]
J. J. Santillan, T. Itani, EUVL Infrastructure Development Ctr., Inc. (Japan)
- 8325 0Q **Understanding dissolution behavior of 193nm photoresists in organic solvent developers**
[8325-26]
S.-H. Lee, J. K. Park, T. Cardolaccia, J. Sun, C. Andes, K. O'Connell, G. G. Barclay, The Dow
Chemical Co. (United States)
- 8325 0R **Critical material properties for pattern collapse mitigation** [8325-27]
G. Winroth, IMEC (Belgium); T. R. Younkin, J. M. Blackwell, Intel Corp. (United States);
R. Gronheid, IMEC (Belgium)
- 8325 0S **Accelerated purge drying to prevent pattern collapse without surfactant rinse for high-aspect ratio resist patterns** [8325-28]
T. Goto, C. Pieczulewski, A. Morita, SOKUDO Co., Ltd. (Japan)

NOVEL MATERIALS AND PROCESSING I

- 8325 0T **Investigation of pattern wiggling for spin-on organic hardmask materials** [8325-29]
G. Wakamatsu, K. Goto, Y. Hishiro, JSR Micro, Inc. (United States); T. Furukawa, S. Murakami, M. Motonari, Y. Yamaguchi, T. Shimokawa, JSR Corp. (Japan); G. Breyta, A. DeSilva, N. Arellano, L. D. Bozano, R. Sooriyakumaran, C. E. Larson, IBM Almaden Research Ctr. (United States); M. Glodde, IBM Thomas J. Watson Research Ctr. (United States)
- 8325 0U **Spin-on-carbon-hardmask with high wiggling resistance** [8325-30]
Y. Someya, T. Shinjo, K. Hashimoto, H. Nishimaki, R. Karasawa, R. Sakamoto, T. Matsumoto, Nissan Chemical Industries, Ltd. (Japan)
- 8325 0V **Substrate and underlayer dependence of sub-32nm e-beam HSQ pillar patterning process for RRAM application** [8325-31]
W.-S. Chen, P.-S. Chen, H.-W. Wei, F. T. Chen, M.-J. Tsai, T.-K. Ku, Industrial Technology Research Institute (Taiwan)
- 8325 0X **Conductive layer for charge dissipation during electron-beam exposures** [8325-33]
L. D. Bozano, R. Sooriyakumaran, L. K. Sundberg, M. I. Sanchez, E. M. Lofano, C. T. Rettner, IBM Almaden Research Ctr. (United States); T. Nagasawa, S. Watanabe, Y. Kawai, Shin-Etsu Chemical Co., Ltd. (Japan); N. Palavesam, Politecnico di Torino (Italy); G. Gandara Montano, Northern Arizona Univ. (United States)

LITHOGRAPHY AT THE INTERSECTION OF OPTICS AND CHEMISTRY: JOINT SESSION WITH CONFERENCE 8326

- 8325 0Z **The saga of lambda: spectral influences throughout lithography generations (Invited Paper)** [8325-35]
B. W. Smith, Rochester Institute of Technology (United States)

EUV MATERIALS, PROCESSING, AND ANALYSIS

- 8325 11 **Patterning development in spin-on hard mask systems for 30nm half-pitch EUV technology** [8325-37]
V. Truffert, I. Pollentier, P. Foubert, F. Lazzarino, IMEC (Belgium); Y. Anno, JSR Micro N.V. (Belgium); C. J. Wilson, M. Ercken, R. Gronheid, S. Demuynck, IMEC (Belgium); X. Buch, JSR Micro N.V. (Belgium)
- 8325 12 **The novel spin-on hard mask and ultrathin UL material for EUVL** [8325-38]
R. Sakamoto, H. Yaguchi, S. Shigaki, S. Sassa, N. Fujitani, T. Endo, R. Onishi, B. C. Ho, Nissan Chemical Industries, Ltd. (Japan)
- 8325 13 **EUV resist processing with flash-lamp** [8325-39]
J. J. Santillan, EUVL Infrastructure Development Ctr., Inc. (Japan); K. Kaneyama, A. Morita, SOKUDO Co., Ltd. (Japan); K. Fuse, H. Kiyama, Daiippon Screen Manufacturing Co., Ltd. (Japan); M. Asai, SOKUDO Co., Ltd. (Japan); T. Itani, EUVL Infrastructure Development Ctr., Inc. (Japan)

- 8325 14 **Stable, fluorinated acid amplifiers for use in EUV lithography** [8325-40]
S. Kruger, College of Nanoscale Science and Engineering, Univ. at Albany (United States);
K. Hosoi, Central Glass Co., Ltd. (Japan); B. Cardineau, College of Nanoscale Science and
Engineering, Univ. at Albany (United States); K. Miyauchi, Central Glass Co., Ltd. (Japan);
R. Brainard, College of Nanoscale Science and Engineering, Univ. at Albany (United States)

NOVEL MATERIALS AND PROCESSING II

- 8325 17 **CD error budget analysis for self-aligned multiple patterning** [8325-43]
K. Oyama, S. Natori, S. Yamauchi, A. Hara, H. Yaegashi, Tokyo Electron Ltd. (Japan)
- 8325 18 **Demonstration of 22nm SRAM features with patternable hafnium oxide-based resist material using electron-beam lithography** [8325-44]
X. Thrun, K.-H. Choi, M. Freitag, Fraunhofer-Ctr. Nanoelektronische Technologien (Germany);
A. Grenville, Inpria Corp. (United States); M. Gutsch, C. Hohle, Fraunhofer-Ctr.
Nanoelektronische Technologien (Germany); J. K. Stowers, Inpria Corp. (United States);
J. W. Bartha, Technische Univ. Dresden (Germany)
- 8325 19 **Direct implant through BARC** [8325-45]
T. Ohashi, M. Umezaki, Y. Hiroi, S. Kimura, Y. Usui, T. Kishioka, Nissan Chemical Industries, Ltd.
(Japan)
- 8325 1A **Focus improvement with NIR absorbing underlayer attenuating substructure reflectivity**
[8325-47]
W.-S. Huang, IBM Microelectronics (United States); D. Goldfarb, IBM Thomas J. Watson
Research Ctr. (United States); W.-K. Li, IBM Microelectronics (United States); M. Glodde, IBM
Thomas J. Watson Research Ctr. (United States); K. Noda, S. Tachibana, M. Ohashi, Shin-Etsu
Chemical Co., Ltd. (Japan); D.-C. Owe-Yang, Shin-Etsu MicroSi, Inc. (United States);
T. Kinsho, Shin-Etsu Chemical Co., Ltd. (Japan)
- 8325 1B **Design, synthesis, and characterization of KrF negative developable bottom anti-reflective coating materials** [8325-48]
S. Liu, K.-J. Chen, W.-S. Huang, S. Holmes, IBM Corp. (United States); K. Huang, N. Fender, JSR
Micro, Inc. (United States); R. Kwong, IBM Corp. (United States); B. Osborn, C. Tang, JSR
Micro, Inc. (United States); C.-H. Wu, IBM Corp. (United States); M. Slezak, JSR Micro, Inc.
(United States)

POSTER SESSION: EUV MATERIALS

- 8325 1D **Limitation of blend type of resist platform on EUV lithography** [8325-51]
T. Hirayama, Tokyo Ohka Kogyo Co., Ltd. (Japan); S. M. Kim, H. S. Na, C. Koh, H. W. Kim,
SAMSUNG Electronics Co., Ltd. (Korea, Republic of)
- 8325 1F **Theoretical study on structural effects of polymer ionization for EUV resist** [8325-53]
M. Endo, S. Tagawa, Osaka Univ. (Japan) and Japan Science and Technology
Agency/CREST (Japan)

- 8325 1G **Investigation of correlation with the octanol water partition coefficient and the sensitivity of negative-tone molecular resists** [8325-54]
M. Echigo, M. Yamakawa, Y. Ochiai, Y. Okada, M. Takasuka, Mitsubishi Gas Chemical Co., Inc. (Japan)
- 8325 1H **A novel single-component resist based on poly (4-hydroxystyrene) applicable for EUV lithography** [8325-55]
J. Liu, Beijing Normal Univ. (China); M. Li, Taiyuan Institute of Technology (China); L. Wang, Beijing Normal Univ. (China)

POSTER SESSION: FUNDAMENTALS

- 8325 1K **Defining and measuring development rates for a stochastic resist** [8325-58]
C. A. Mack, Lithoguru.com (United States)
- 8325 1L **Diffusion of acid from resist to Si-hardmask layer** [8325-59]
M. Shirai, H. Takeda, T. Hatsuse, H. Okamura, Osaka Prefecture Univ. (Japan); H. Wakayama, M. Nakajima, Nissan Chemical Industries, Ltd. (Japan)
- 8325 1M **LWR reduction by photoresist formulation optimization for 193nm immersion lithography** [8325-60]
D. S.-H. Hsu, W.-H. Hsieh, C.-Y. Huang, W.-B. Wu, C.-L. Shih, Nanya Technology Corp. (Taiwan)
- 8325 1N **Observation of swelling behavior of ArF resist during development by using QCM method** [8325-61]
A. Sekiguchi, H. Konishi, M. Isono, Litho Tech Japan Co., Ltd. (Japan)
- 8325 1O **Study of the lithography characteristics of novolak resist at different PAC concentrations** [8325-62]
A. Sekiguchi, Litho Tech Japan Co., Ltd. (Japan); A. Nakao, H. Horibe, Kanazawa Institute of Technology (Japan); H. Tanaka, AZ Electronic Materials K.K. (Japan)

POSTER SESSION: NOVEL RESIST MATERIALS

- 8325 1Q **Synthesis and photopolymerization kinetics of a novel oxime ester sulfonic acid photoacid generator** [8325-65]
Y.-L. Pang, Y.-Q. Zou, Beijing Normal Univ. (China)
- 8325 1S **Synthesis of stable acid amplifiers that produce strong highly-fluorinated polymer-bound acid** [8325-67]
K. Hosoi, Central Glass Co., Ltd. (Japan); B. Cardineau, W. Earley, S. Kruger, College of Nanoscale Science & Engineering, Univ. at Albany (United States); K. Miyauchi, Central Glass Co., Ltd. (Japan); R. Brainard, College of Nanoscale Science & Engineering, Univ. at Albany (United States)
- 8325 1T **Ionic carbamate photoacid/photobase generators for the advancement of dual-tone photolithography** [8325-68]
G. L. Hallett-Tapley, T.-L. Wee, Univ. of Ottawa (Canada); J. Eldo, E. A. Jackson, SAFC Hitech (United States); J. M. Blackwell, Intel Corp. (United States); J. C. Scaiano, Univ. of Ottawa (Canada)

- 8325 1U **Positive-tone chemically amplified fullerene resist** [8325-69]
J. Manyam, A. Frommhold, D. X. Yang, A. McClelland, M. Manickam, J. A. Preece, R. E. Palmer, A. P. G. Robinson, The Univ. of Birmingham (United Kingdom)
- 8325 1V **Synthesize and polymerization of novel photocurable vinyl ether monomers containing perfluorinated aromatic units** [8325-70]
W. Li, Y. Q. Zou, Beijing Normal Univ. (China)
- 8325 1W **Reduced Zeta potential through use of cationic adhesion promoter for improved resist process performance and minimizing material consumption** [8325-95]
L. Hodgson, MOXTEK, Inc. (United States); A. Thompson, DisChem, Inc. (United States)
- 8325 1X **Resist surface crosslinking using amine-based reactive rinses to mitigate pattern collapse in thin film lithography** [8325-97]
W.-M. Yeh, R. A. Lawson, L. M. Tolbert, C. L. Henderson, Georgia Institute of Technology (United States)
- 8325 1Y **Application of aziridine reactive rinses in a post-development process to reduce photoresist pattern collapse** [8325-98]
W.-M. Yeh, R. A. Lawson, L. M. Tolbert, C. L. Henderson, Georgia Institute of Technology (United States)

POSTER SESSION: NOVEL PROCESSING

- 8325 1Z **Characteristics analysis of RELACS process from an OPC point of view** [8325-46]
J. Choi, M. Yoo, C. Park, C. Oh, C. Kim, H. Yang, D. Yim, Hynix Semiconductor Inc. (Korea, Republic of)
- 8325 23 **Development of Si-HM for NTD process** [8325-73]
W. L. Huang, Y. C. Huang, B. J. Lu, Y. J. Wang, Y. S. Lin, C. C. Yu, United Microelectronics Corp. (Taiwan); S. Takeda, Y. Someya, M. Nakajima, Y. Kanno, H. Wakayama, R. Sakamoto, Nissan Chemical Industries, Ltd. (Japan)
- 8325 24 **Negative-tone development of photoresists in environmentally friendly silicone fluids** [8325-74]
C. Y. Ouyang, Cornell Univ. (United States); J.-K. Lee, Inha Univ. (Korea, Republic of); C. K. Ober, Cornell Univ. (United States)
- 8325 25 **High-etching selectivity of spin-on-carbon hard mask process for 22nm node and beyond** [8325-76]
F. Iwao, S. Shimura, H. Kyouda, Tokyo Electron Kyushu Ltd. (Japan); K. Oyama, S. Yamauchi, A. Hara, S. Natori, H. Yaegashi, Tokyo Electron Ltd. (Japan)
- 8325 26 **Applicability of double-patterning process for fine-hole patterns** [8325-77]
S. Yamauchi, A. Hara, K. Oyama, S. Natori, H. Yaegashi, Tokyo Electron Ltd. (Japan)
- 8325 27 **Plasmon mediated polymerization on the surface of silver nanoparticles for advancements in photolithographic patterning** [8325-78]
K. G. Stamplecoskie, J. C. Scaiano, Univ. of Ottawa (Canada)

- 8325 28 **Advanced multi-patterning using resist core spacer process for 22nm node and beyond** [8325-79]
Y. Kuwahara, S. Shimura, H. Kyouda, Tokyo Electron Kyushu Ltd. (Japan); K. Oyama, S. Yamauchi, A. Hara, S. Natori, H. Yaegashi, Tokyo Electron Ltd. (Japan)
- 8325 2A **Combinatorial process optimization for negative photo-imageable spin-on dielectrics and investigation of post-apply bake and post-exposure bake interactions** [8325-81]
J. Kim, R. M. Zhang, E. Wolfer, B. K. Patel, M. Toukhy, Z. Bogusz, AZ Electronic Materials USA Corp. (United States); T. Nagahara, AZ Electronic Materials K.K. (Japan)
- 8325 2B **Tunable resin reactivity of spin-on dielectric by controlling synthesis process** [8325-82]
K. W. Han, H.-J. Song, M.-Y. Kim, E. S. Park, H. C. Yoon, G. E. Kim, S. H. Lim, S. K. Kim, Samsung Cheil Industries Inc. (Korea, Republic of)
- 8325 2D **KrF resists for implant layers patterning extreme high-aspect ratio structures with a double focal plane exposure technique** [8325-84]
G. Raffaelli, F. Ferri, Micron Technology Italia S.r.l. (Italy); S. Volpi, FUJIFILM Electronic Materials (Europe) S.r.l. (Italy); C. Hong, FUJIFILM Electronic Materials U.S.A., Inc. (United States)
- 8325 2E **Gray-level 3D resist process and its application** [8325-85]
Y.-C. Ting, Far East Univ. (Taiwan); S.-L. Shy, A. Liu, C.-S. Wu, C. C. Chen, National Nano Device Labs. (Taiwan)
- 8325 2F **Measurement and reduction of micro-bubble formation in high-viscosity fluids** [8325-96]
G. Tom, W. Liu, ATMI, Inc. (United States)

POSTER SESSION: DEFECTIVITY AND MANUFACTURING

- 8325 2G **Blob defect prevention in 193nm topcoat-free immersion lithography** [8325-86]
D. Wang, J. Liu, D. Kang, C. Liu, T. Estelle, C.-B. Xu, G. Barclay, P. Trefonas, The Dow Chemical Co. (United States)
- 8325 2H **Solvent pre-wetting as an effective start-up method for point-of-use filter** [8325-87]
T. Umeda, Nihon Pall Ltd. (Japan); S. Sugiyama, T. Nakamura, M. Momota, FUJIFILM Corp. (Japan); M. Sevegney, Pall Corp. (United States); S. Tsuzuki, T. Numaguchi, Nihon Pall Ltd. (Japan)
- 8325 2I **The filter adsorption mechanism in photoresist materials** [8325-88]
T. Kohyama, Nihon Entegris K. K. (Japan)
- 8325 2J **Post-developed defect in word-line SADP process** [8325-89]
P. J. Cheng, F. N. Tsai, C. C. Yang, E. Yang, T. H. Yang, K. C. Chen, C.-Y. Lu, Macronix International Co., Ltd. (Taiwan)
- 8325 2K **Pattern dependent satellite defects in via lithography** [8325-91]
C.-C. Yu, M. Yang, E. Yang, T. H. Yang, K. C. Chen, C.-Y. Lu, Macronix International Co., Ltd. (Taiwan)
- 8325 2L **Resist process optimization for further defect reduction** [8325-92]
K. Tanaka, T. Iseki, H. Marumoto, K. Takayanagi, Y. Yoshida, R. Uemura, K. Yoshihara, Tokyo Electron Kyushu Ltd. (Japan)

- 8325 2M **Effects of nylon filter properties on contact-hole photoresist imaging performance and defectivity** [8325-93]
M. Cronin, Entegris, Inc. (United States); N. Vitorino, V. Monreal, J. Zook, AZ Electronic Materials USA Corp. (United States)

Author Index

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Yoshio Kawai, Shin-Etsu Chemical Company, Ltd. (Japan)
Qinghuang Lin, IBM Thomas J. Watson Research Center (United States)
Nobuyuki N. Matsuzawa, Sony Corporation (Japan)
Dah-Chung Owe-Yang, Shin-Etsu MicroSi, Inc. (United States)
Daniel P. Sanders, IBM Almaden Research Center (United States)
Plamen Tzviatkov, FUJIFILM Electronic Materials U.S.A., Inc. (United States)
Todd R. Younkin, Intel Corporation (Belgium)

Session Chairs

- 1 Keynote Session
Mark H. Somervell, Tokyo Electron America, Inc. (United States)
Thomas I. Wallow, GLOBALFOUNDRIES Inc. (United States)

- 2 Negative Tone Processing
Scott W. Jessen, Texas Instruments Inc. (United States)
Plamen Tzviatkov, FUJIFILM Electronic Materials U.S.A., Inc. (United States)
- 3 EUV: Joint Session with Conference 8322
Yoshio Kawai, Shin-Etsu Chemical Co., Ltd. (Japan)
- 4 Optical Extensions
Ralph R. Dammel, AZ Electronic Materials USA Corporation (United States)
Clifford L. Henderson, Georgia Institute of Technology (United States)
- 5 Directed Self-Assembly I: Resist Processing: Joint Session with Conference 8323
Daniel P. Sanders, IBM Almaden Research Center (United States)
- 6 Simulation of Resist Processes
Clifford L. Henderson, Georgia Institute of Technology (United States)
Todd R. Younkin, Intel Corporation (Belgium)
- 7 Resist Fundamentals
Plamen Tzviatkov, FUJIFILM Electronic Materials U.S.A., Inc. (United States)
Luisa D. Bozano, IBM Almaden Research Center (United States)
- 8 Novel Materials and Processing I
Ramakrishnan Ayothi, JSR Micro, Inc. (United States)
Douglas J. Guerrero, Brewer Science, Inc. (United States)
- 9 Lithography at the Intersection of Optics and Chemistry: Joint Session with Conference 8326
Mark H. Somervell, Tokyo Electron America, Inc. (United States)
Will Conley, Dynamic Intelligence (United States)
- 10 EUV Materials, Processing, and Analysis
Christoph K. Hohle, Fraunhofer-Center Nanoelektronische Technologien (Germany)
Nobuyuki N. Matsuzawa, Sony Corporation (Japan)
- 11 Novel Materials and Processing II
Dah-Chung Owe-Yang, Shin-Etsu MicroSi, Inc. (United States)
George G. Barclay, Dow Advanced Materials (United States)